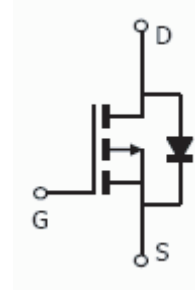


P-Channel Enhancement Mode Power MOSFET

Description

The RM27P30LD uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.



Schematic diagram

General Features

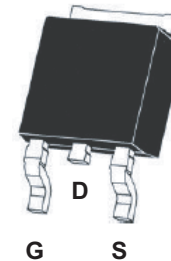
- $V_{DS} = -30V, I_D = -27A$
 $R_{DS(ON)} < 30m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 55m\Omega @ V_{GS} = -4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation



Application

- Power switching application
- Hard switched and high frequency circuits
- DC-DC Converter
- Halogen-free

Marking and pin assignment



TO-252-2L top view

100% UIS TESTED!

100% ΔV_{ds} TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
27P30	RM27P30LD	TO-252-2L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-27	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	-17	A
Pulsed Drain Current	I_{DM}	-54	A
Maximum Power Dissipation($T_C = 25^\circ C$)	P_D	31.3	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance ,Junction-to-Case ^(Note 2)	$R_{\theta JC}$	4	$^\circ C/W$
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Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-	-2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D = -12A	-	-	30	mΩ
		V _{GS} =-4.5V, I _D = -6A	-	-	55	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-12A	-	15	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, F=1.0MHz	-	930	-	PF
Output Capacitance	C _{oss}		-	148	-	PF
Reverse Transfer Capacitance	C _{rss}		-	115	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-24V, I _D =-1A V _{GS} =-10V, R _{GEN} =3.3Ω	-	1.64	-	nS
Turn-on Rise Time	t _r		-	20.2	-	nS
Turn-Off Delay Time	t _{d(off)}		-	55	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =-20V, I _D =-12A, V _{GS} =-4.5V	-	9.8	-	nC
Gate-Source Charge	Q _{gs}		-	2.2	-	nC
Gate-Drain Charge	Q _{gd}		-	3.4	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-1A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-27	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

RATING AND CHARACTERISTICS CURVES (RM27P30LD)

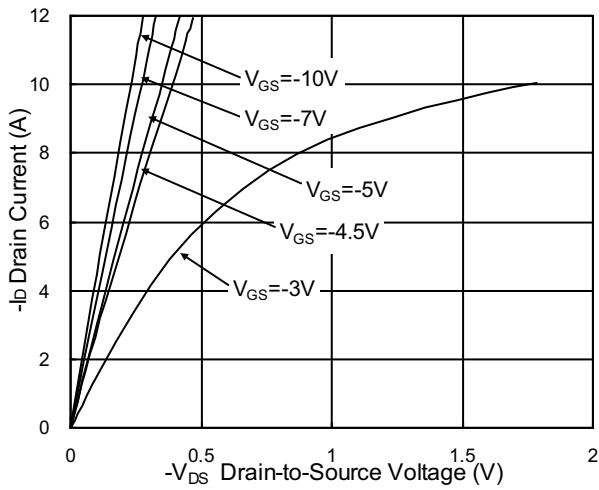


Fig.1 Typical Output Characteristics

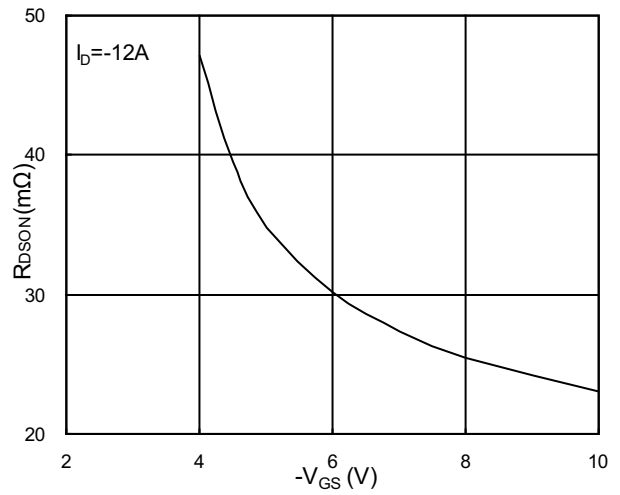


Fig.2 On-Resistance v.s Gate-Source

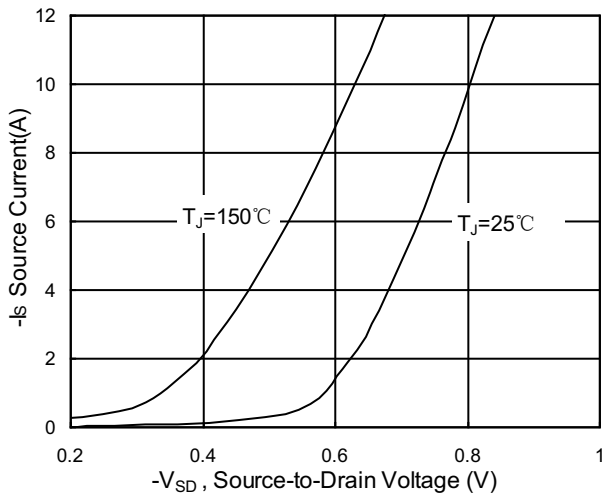


Fig.3 Forward Characteristics of Reverse

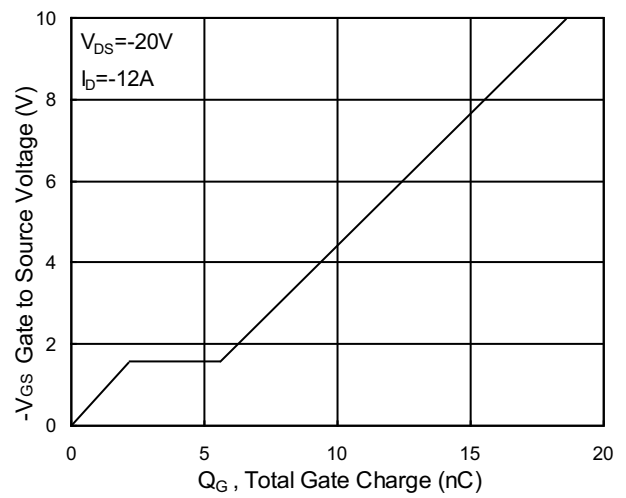


Fig.4 Gate-Charge Characteristics

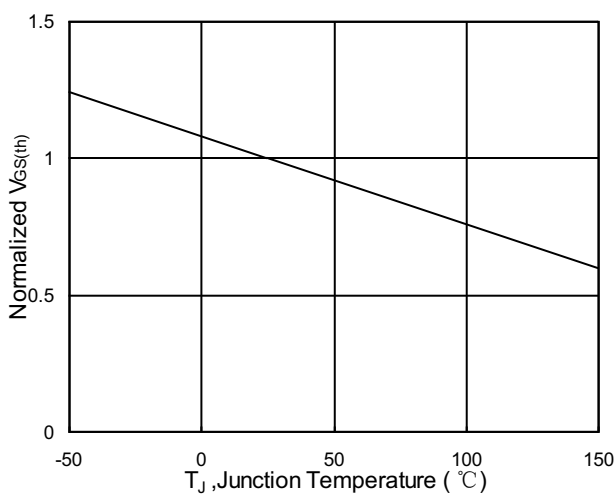


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

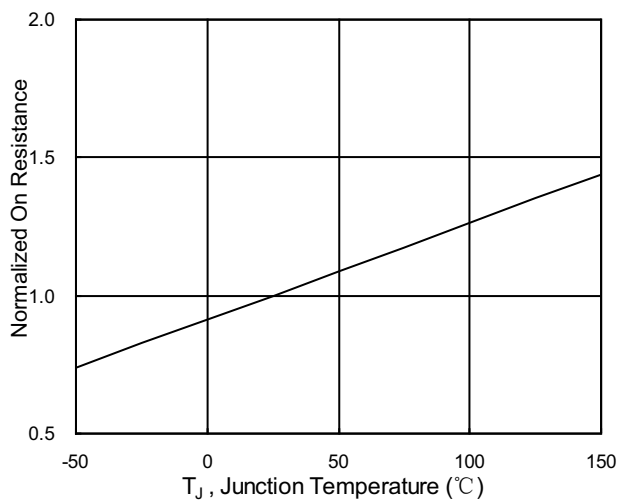


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

RATING AND CHARACTERISTICS CURVES (RM27P30LD)

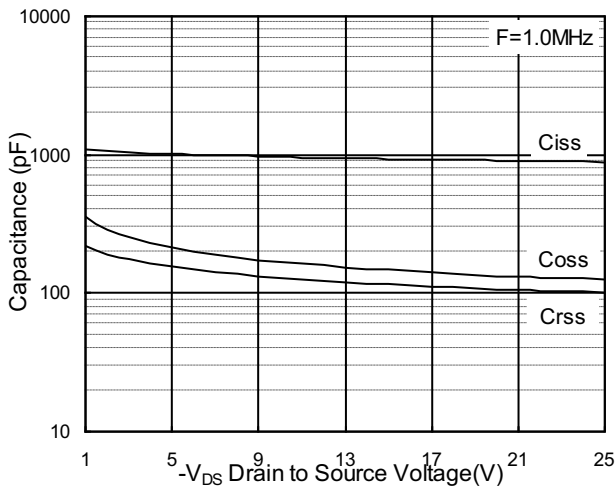


Fig.7 Capacitance

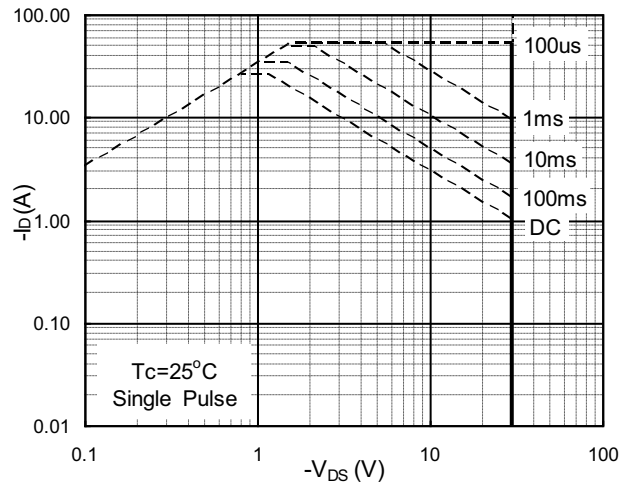


Fig.8 Safe Operating Area

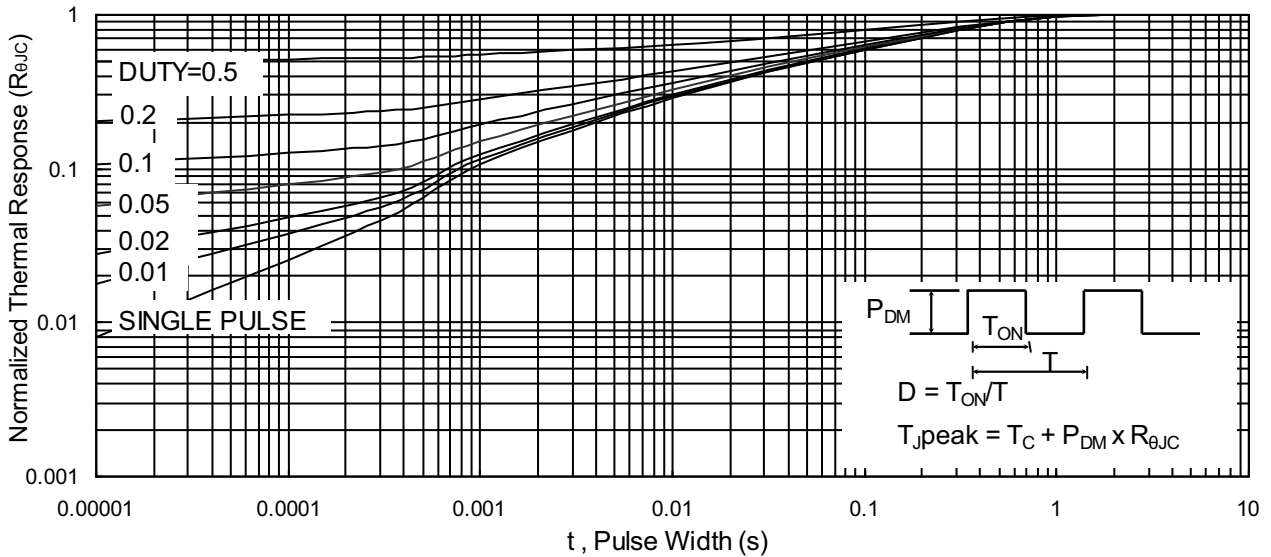


Fig.9 Normalized Maximum Transient Thermal Impedance

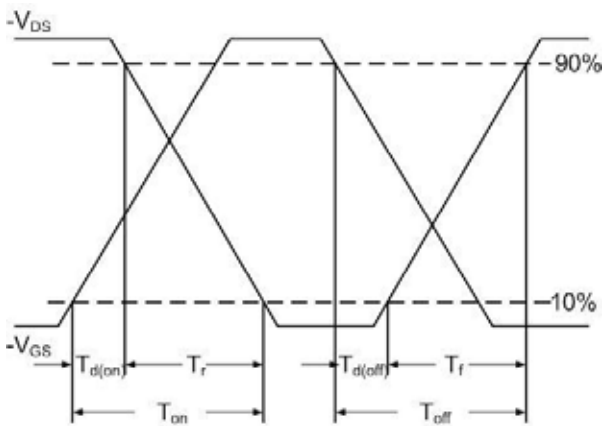


Fig.10 Switching Time Waveform

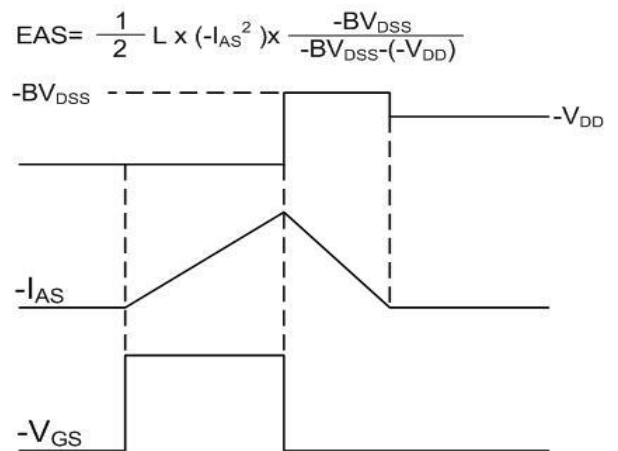
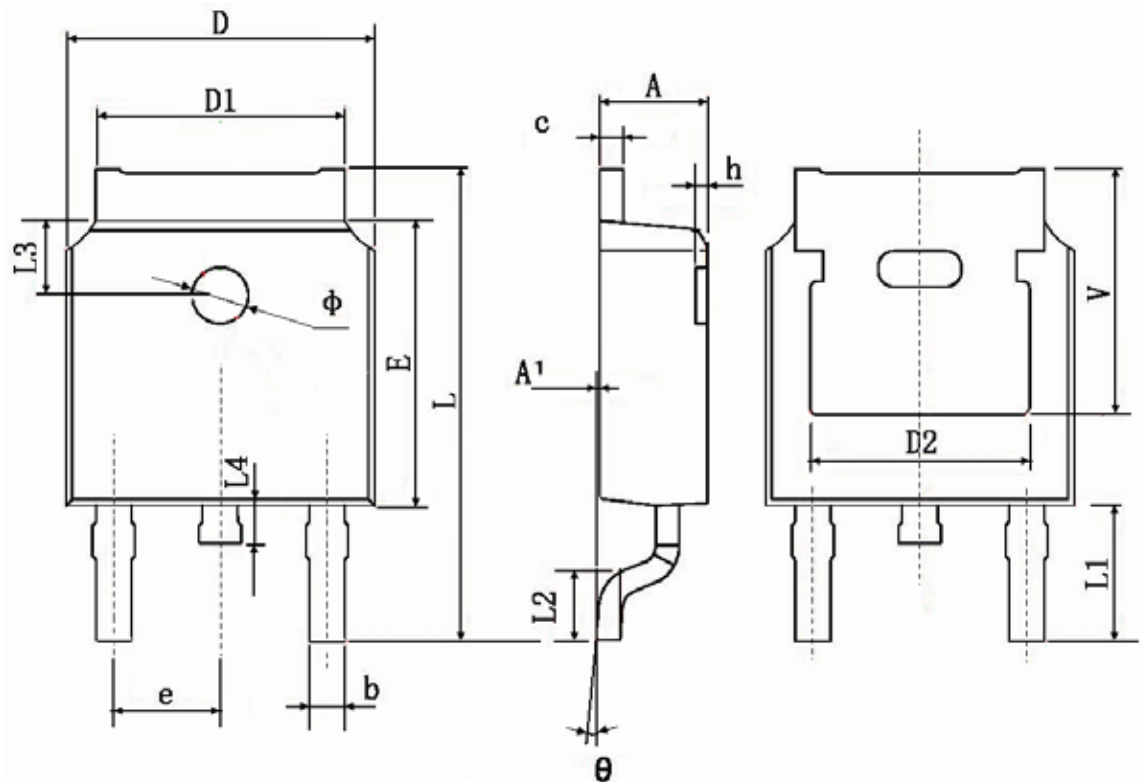


Fig.11 Unclamped Inductive Switching Waveform

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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